## Bi-Directional Triode Thyristor

## Features

- Repetitive Peak Off-State Voltage : 600V
-R.M.S On-State Current ( $\left.\mathrm{I}_{\mathrm{T}(\mathrm{RMS})}=8 \mathrm{~A}\right)$
- High Commutation dv/dt
- Isolation Voltage ( $\mathrm{V}_{\text {ISO }}=1500 \mathrm{~V}$ AC $)$
 This device is approved to comply with applicable requirements by Underwriters Laboratories Inc.

Absolute Maximum Ratings ( $\mathrm{T}_{\mathrm{J}}=25^{\circ} \mathrm{C}$ unless otherwise specified)

| Symbol | Parameter | Condition | Ratings | Units |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {DRM }}$ | Repetitive Peak Off-State Voltage |  | 800 | V |
| $\mathrm{I}_{\mathrm{T} \text { (RMS) }}$ | R.M.S On-State Current | $\mathrm{T}_{\mathrm{C}}=89^{\circ} \mathrm{C}$ | 8.0 | A |
| $\mathrm{I}_{\text {TSM }}$ | Surge On-State Current | One Cycle, $50 \mathrm{~Hz} / 60 \mathrm{~Hz}$, Peak, Non-Repetitive | 80/88 | A |
| $\mathrm{I}^{2} \mathrm{t}$ | $1^{2} \mathrm{t}$ |  | 32 | $A^{2} s$ |
| $\mathrm{P}_{\mathrm{GM}}$ | Peak Gate Power Dissipation |  | 5.0 | W |
| $\mathrm{P}_{\mathrm{G}(\mathrm{AV})}$ | Average Gate Power Dissipation |  | 0.5 | W |
| $\mathrm{I}_{\mathrm{GM}}$ | Peak Gate Current |  | 2.0 | A |
| $\mathrm{V}_{\mathrm{GM}}$ | Peak Gate Voltage |  | 10 | V |
| $\mathrm{V}_{\text {ISO }}$ | Isolation Breakdown Voltage(R.M.S.) | A.C. 1 minute | 1500 | V |
| $\mathrm{T}_{\mathrm{J}}$ | Operating Junction Temperature |  | - $40 \sim 125$ | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {STG }}$ | Storage Temperature |  | - $40 \sim 150$ | ${ }^{\circ} \mathrm{C}$ |
|  | Mass |  | 2.0 | g |

## STF10A80

## Electrical Characteristics

| Symbol | Items |  | Conditions | Ratings |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | Min. | Typ. | Max. |  |
| $\mathrm{I}_{\text {DRM }}$ | Rep Cur | ive Peak Off-State |  | $V_{D}=V_{D R M}$, Single Phase, Half Wave $\mathrm{T}_{\mathrm{J}}=125^{\circ} \mathrm{C}$ | - | - | 2.0 | mA |
| $\mathrm{V}_{\text {TM }}$ | Pea | On-State Voltage | $\mathrm{I}_{\mathrm{T}}=15 \mathrm{~A}$, Inst. Measurement | - | - | 1.6 | V |
| $\mathrm{I}^{+}{ }_{\text {GT1 }}$ | 1 | Gate Trigger Current | $\mathrm{V}_{\mathrm{D}}=6 \mathrm{~V}, \mathrm{R}_{\mathrm{L}}=10 \Omega$ | - | - | 30 | mA |
| $1^{-}{ }_{\text {GT1 }}$ | II |  |  | - | - | 30 |  |
| $1{ }^{-} \mathrm{GT3}$ | III |  |  | - | - | 30 |  |
| $\mathrm{V}^{+}{ }_{\mathrm{GT1}}$ | 1 | Gate Trigger Voltage | $\mathrm{V}_{\mathrm{D}}=6 \mathrm{~V}, \mathrm{R}_{\mathrm{L}}=10 \Omega$ | - | - | 1.5 | V |
| $\mathrm{V}^{-} \mathrm{GT1}$ | II |  |  | - | - | 1.5 |  |
| $\mathrm{V}^{-} \mathrm{GT3}$ | III |  |  | - | - | 1.5 |  |
| $V_{G D}$ | Non-Trigger Gate Voltage |  | $\mathrm{T}_{\mathrm{J}}=125^{\circ} \mathrm{C}, \mathrm{V}_{\mathrm{D}}=1 / 2 \mathrm{~V}_{\text {DRM }}$ | 0.2 | - | - | V |
| (dv/dt)c | Critical Rate of Rise Off-State Voltage at Commutation |  | $\begin{aligned} & \mathrm{T}_{\mathrm{J}}=125^{\circ} \mathrm{C},[\mathrm{di} / \mathrm{dt}] \mathrm{c}=-4.0 \mathrm{~A} / \mathrm{ms}, \\ & \mathrm{~V}_{\mathrm{D}}=2 / 3 \mathrm{~V}_{\mathrm{DRM}} \end{aligned}$ | 10 | - | - | $\mathrm{V} / \mu \mathrm{s}$ |
| $\mathrm{I}_{\mathrm{H}}$ | Holding Current |  |  | - | 15 | - | mA |
| $\mathrm{R}_{\mathrm{th}(\mathrm{j} \mathrm{c})}$ | Thermal Impedance |  | Junction to case | - | - | 3.7 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

